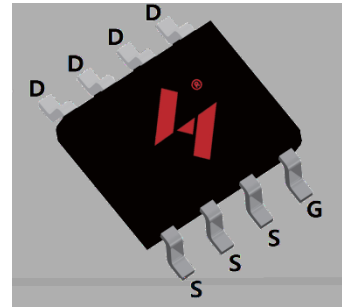


P-Channel Enhancement Mode MOSFET

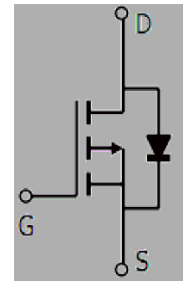
: YUh i fY8YgWf]dh]cb

- 30V/-12A
- $R_{DS(ON)} = 10.8\text{ m}\Omega$ (typ.) @ $V_{GS} = -10V$
- $R_{DS(ON)} = 14.6\text{ m}\Omega$ (typ.) @ $V_{GS} = -4.5V$
- 100% Avalanche Tested
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

D]b' 8YgWf]dh]cb



SOP8L"



P-Channel MOSFET

5dd`]WUh]cbg`

- Power Management DC/DC
- Switching application

CfXYf]b [`UbX' AuF_]b [`=bZcf a Uh]cb

S HY12P03 YYXXXJWW G	Package Code	S: SOP-8L	
	Date Code	YYXXX WW	Assembly Material

P [c^kA PWCEYQA | ^æãÈ-!^A] : [a~&c^A& [} cæã } A { [[ãã } * A& [{] [~ } a•Dãã^Aæccæ&@A { æc^iææ | •Aæ } ããF€€ÃA { æcc^Acã } A] | æc^A
 V^! { ãÈPæcã [] A-ã } ã•@L , @ã&@Aæ!^A~ || ^A& [{] |ãæ } cA , æc@AÜ [PÙÈA PWCEYQA | ^æãÈ-!^A] : [a~&c^A { ^Acã [i^A^æ&^Aãc@^A | ^æãÈ
 Ø | ^A^! ^~ ã! ^È { ^ } c^A [-AQÜÖDRÒÖÖÖÄRÈÜVÖÈ€€Ä- [i^A T ÛŠA& | æ••ã-ã&æcã [} Aæcã | ^æãÈ-!^A] ^æ\A | ^- [[, ^Ac { }] ^!æc~ | ^ÈA
 PWCEYQA ãã^ã } ^•Aã | ^ã } +Ac [A { ^æ } A | ^æãÈ-!^A ÇÜ [PÙA& [{] |ãæ } cDãæ } ãA@æ [*^ } A-!^A ÇÓ!A : i^AÖ | Aã [^•A } [c^A^æ&^Aã
 J€€] { Aã^A , ^ã* @cãã } A@ [{ [*^ } ^ [~ •A { æc^iææ | Aæ } ããc [cæ | A [-AÓ!Aæ } ããÖ | Aã [^•A } [c^A^æ&^Aã F [€€] { Aã^A , ^ã* @cDÈA

PWCEYQA | ^•A | Ç^•Ac@^A iã * @cAc [A { æ^A&@æ } * ^•ÈA& [! | ^&cã [] •ÈA^ } @æ } ^ { ^ } c•ÈA { [ãã-ã&æcã [] •ÈAæ } ããã [] : [Ç^ { ^A } c^Ac [A
 c@ã•A] iÈ [a~&c^Aæ } ãD [i^Ac [Ac@ã•Aã [&~ { ^ } c^Aæcãæ } ^Acã { ^A , æc@ [~ cA } [cã&^È

<M%&D\$' S

5Vgc` i hY' AUI] a i a 'FUh]b [g'

Gma Vc`	DUfUa YhYf	FUh]b[I b]h
---------	------------	--------	-------

<M%&D\$' S

9`YWhf]WU`7 \UfUWhYf]gh]Wg`fl7 cbh"L` (Tc =25°C Unless Otherwise Noted)

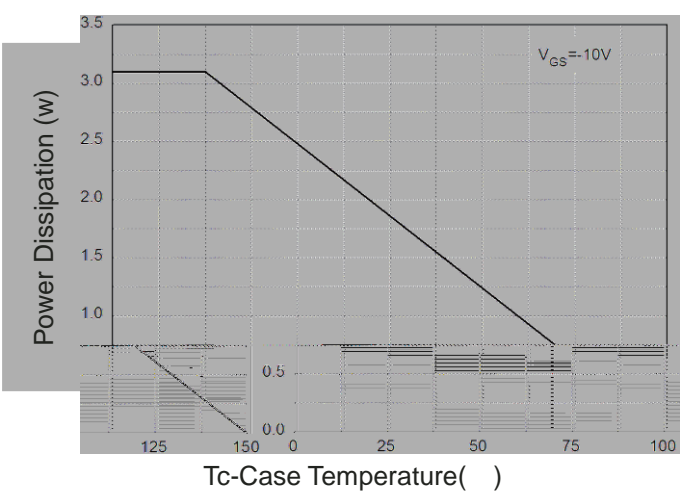
Gm a Vc`	DUfU a YhYf	HYgh`7 cbX]h]cbg	<M%&D\$'			I b]h
			A]b	Hmd"	AUI	
8mbU a]W`7 \UfUWhYf]gh]Wg						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1 MHz	-	2.4	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz	-	2350	-	pF
C _{oss}	Output Capacitance		-	330	-	
C _{rss}	Reverse Transfer Capacitance		-	139	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-15V, R _G =1 I _{DS} =-12A, V _{GS} =-10V	-	11	-	ns
T _r	Turn-on Rise Time		-	9	-	
t _{d(OFF)}	Turn-off Delay Time		-	25	-	
T _f	Turn-off Fall Time		-	13	-	
; UhY`7 \Uf [Y`7 \UfUWhYf]gh]Wg						
Q _g	Total Gate Charge	V _{DS} = -24V, V _{GS} = -10V I _D = -12A,	-	34	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	
Q _{gd}	Gate-Drain Charge		-	8	-	

Note: *Pulse test pulse width 300us duty cycle 2%

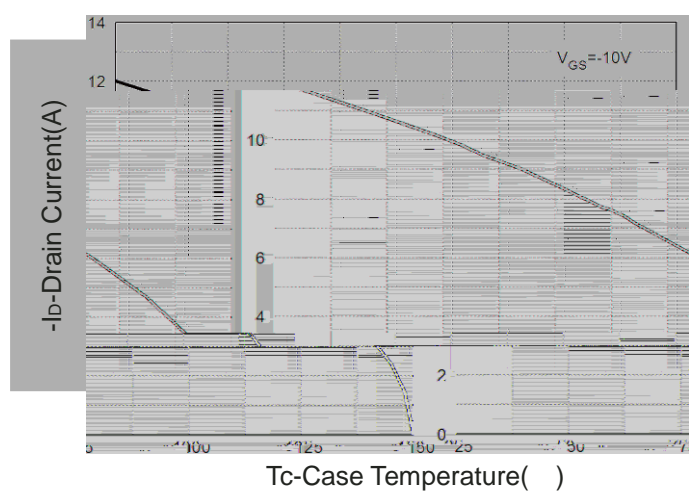
<M%&D\$' G

Hmd]WU` CdYfUh]b ['7 \UfUWhYf]gh]Wg

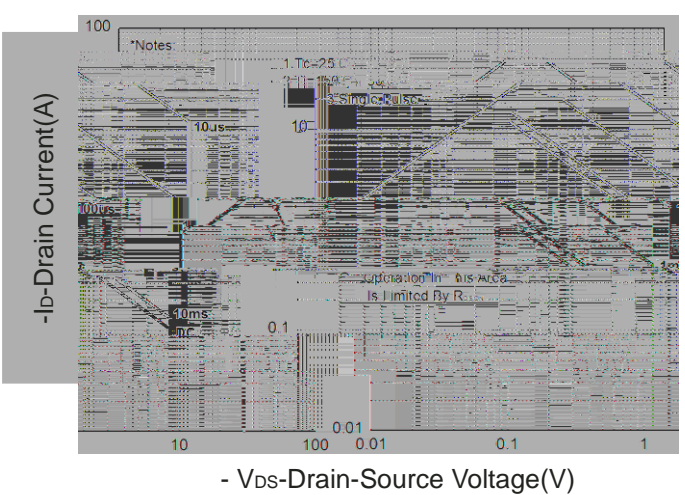
:][i fY%. 'DckYf' 8]gg]dUh]cb



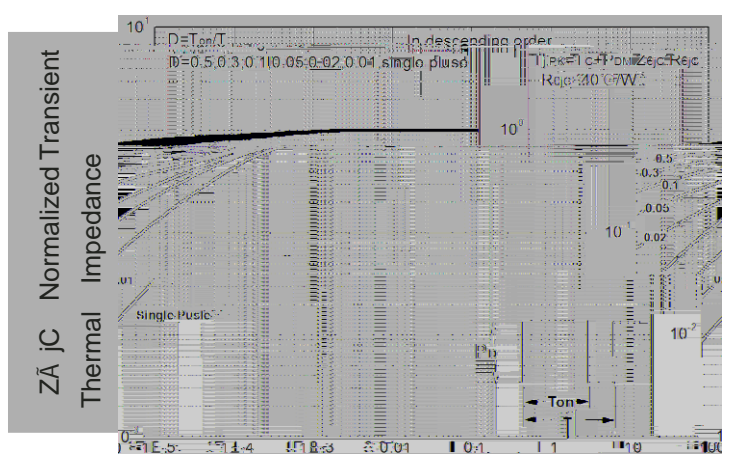
:][i fY&. '8fU]b' 7 i ffYbh



:][i fY' . 'GUZY' CdYfUh]cb' 5fYU'



:][i fY' (. 'H\Yf a U` HfUbg]Ybh' = a dYXUbWY'

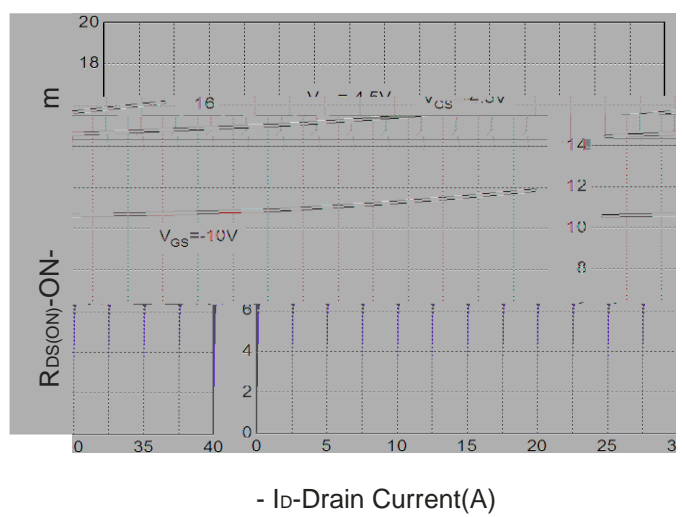
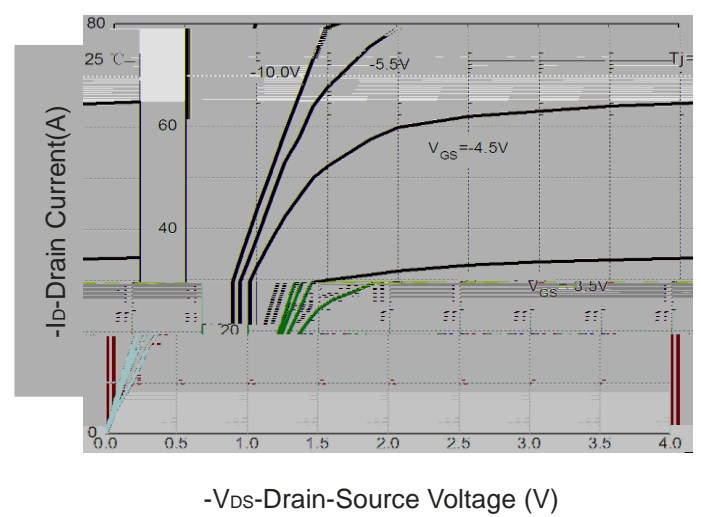


- VDS-Drain-Source Voltage(V)

Maximum Effective Transient Thermal Impedance, Junction-to-Case

:][i fY') . 'C i h d i h' 7 \UfUWhYf]gh]Wg

:][i fY' * . '8fU]b!Gc i fWY' Cb' FYg]ghUbWY'

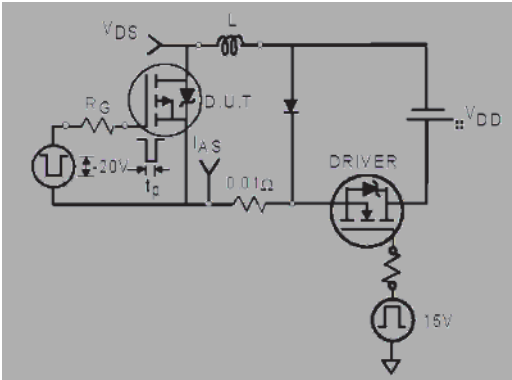


-VDS-Drain-Source Voltage (V)

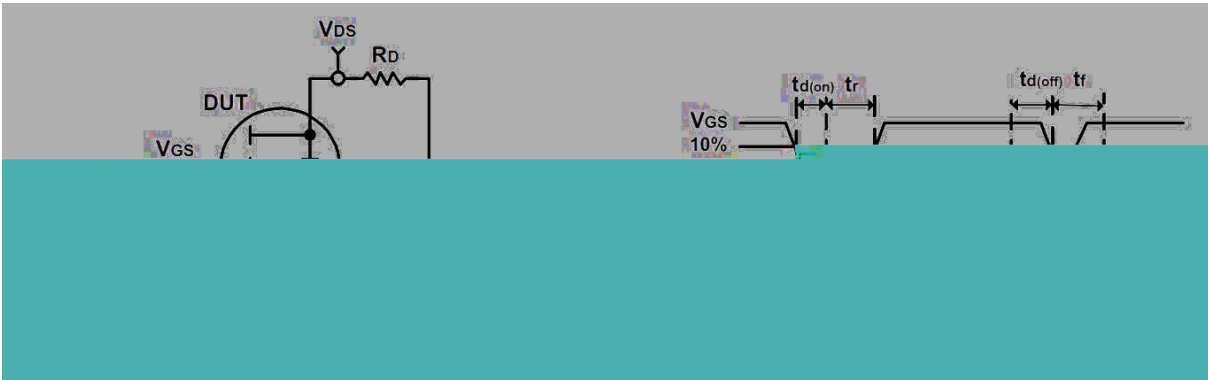
- ID-Drain Current(A)

Measurement

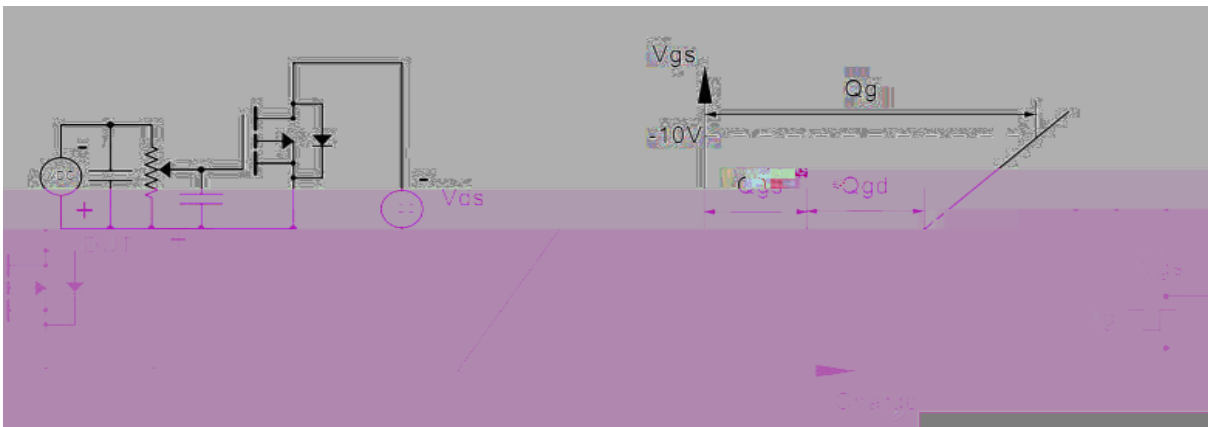
5. Switching Characteristics



6. Switching Time



7. Switching Energy



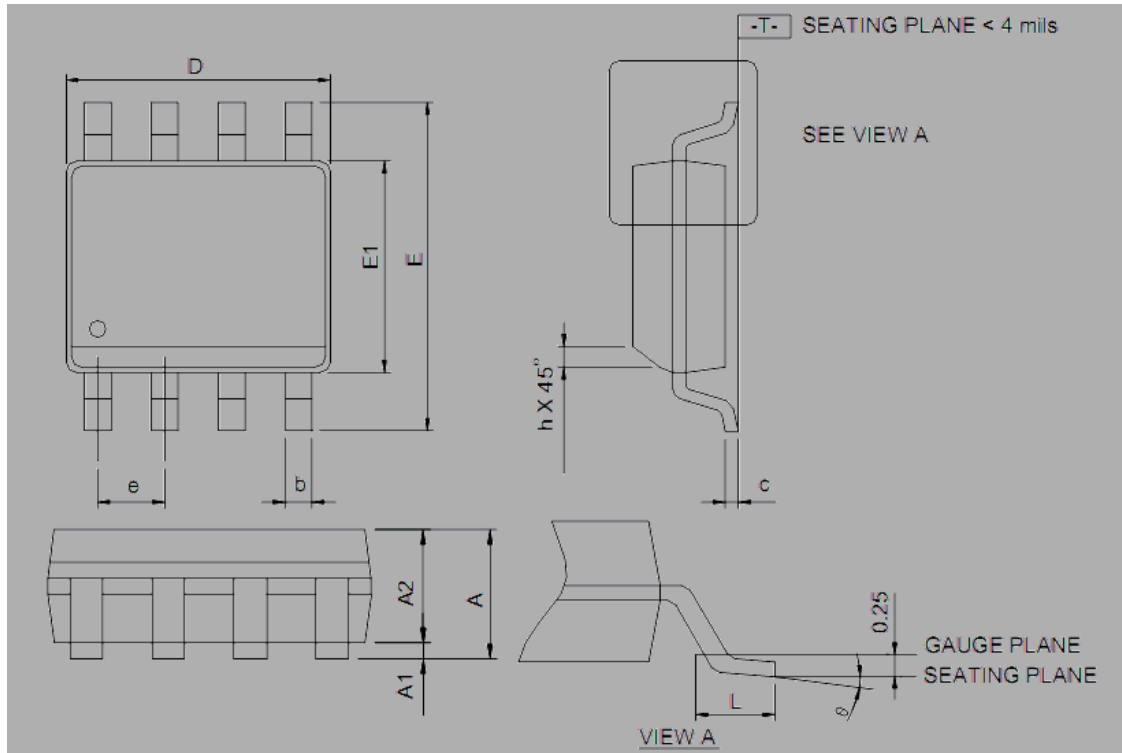
Microelectronics

Microelectronics

DUW_U[Y'HmdY	I b]h	E i Ubh]hm
SOP-8L	Reel	2500

DUW_U[Y'=bZcf a Uh]cb

GCD!,@

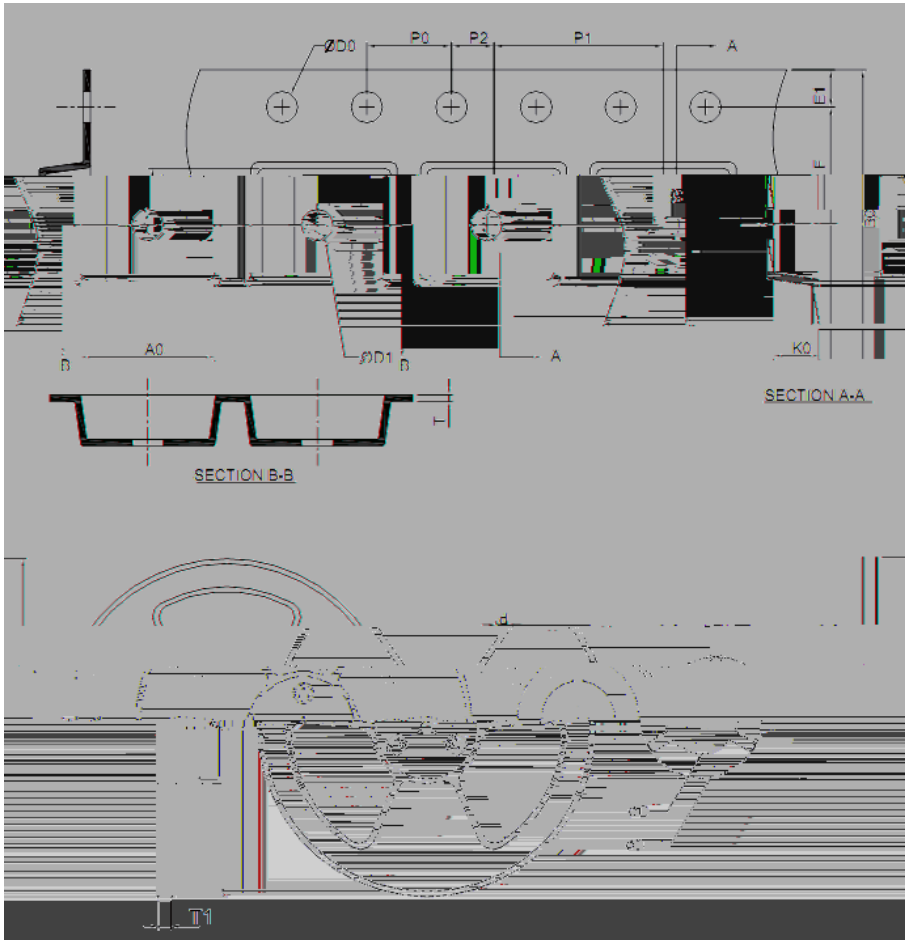


Symbol	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157

RECOMMENDED LAND PATTERN

<M%&D\$' G

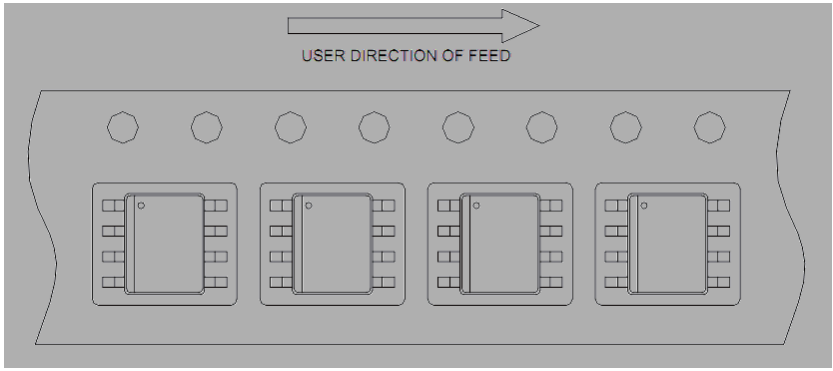
7Uff]Yf'HUdY'/'FYY'8]a Ybg]cbg



Application	A	H	T1	C	d	D	W	E1	F
SOP8L	330.0 2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 0.30	1.75 0.10	5.5 0.05
	P0	P1	P2	P0	P1	T1	A0	P0	K0
	2.10 0.20	4.0 0.10	8.0 0.10	2.0 0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 0.20	5.20 0.20

(mm)

HUd]b ['8]fYWh]cb'=bZcf a Uh]cb



<M%&D\$' S

7`Ugg]Z]WUh]cb`FYZ`ck`DfcZ]`Yg

DfcZ]`Y` : YUhi fY	Gb!DV`9 ihYWh]W` 5ggYa V`m	DV! : fYY` 5ggYa V`m
DfY\YUh` / `GcU_		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*		

7 i g h c a Y f ' G Y f j j W Y '

Worldwide Sales and Service: sales@hymexa.com

Technical Support: Technology@hymexa.com

Xi'an Huayi Microelectronics Co., Ltd.

No.8928,Shangji Road,Economic and Technological Development Zone,Xi'an,China TEL:

(86-029) 86685706

FAX: (86-029) 86685705

E-mail:sales@hymexa.com

Web net: www.hymexa.com